

2SK3032 (Tentative)

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive
- High electrostatic breakdown voltage

■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

■ Absolute Maximum Ratings (T_C = 25°C)

Parameter	Symbol	Rated	Unit	
Drain to Source breakdown voltage	V _{DSS}	100	V	
Gate to Source voltage	V _{GSS}	±20	V	
Drain current	DC	I _D	±25	A
	Pulse	I _{DP}	±50	A
Avalanche energy capacity	EAS*	31.25	mJ	
Allowable power dissipation	T _C = 25°C	P _D	10	W
	T _a = 25°C		1	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

* L = 0.1mH, I_L = 25A, 1 pulse

■ Electrical Characteristics (T_C = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0			10	μA
Gate to Source leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0			±10	μA
Drain to Source breakdown voltage	V _{DSS}	I _D = 1mA, V _{GS} = 0	100			V
Gate threshold voltage	V _{th}	V _{DS} = 10V, I _D = 1mA	1		2.5	V
Drain to Source ON-resistance	R _{DS(on)1}	V _{GS} = 10V, I _D = 12A		64	100	mΩ
	R _{DS(on)2}	V _{GS} = 4V, I _D = 12A		75	120	mΩ
Forward transfer admittance	Y _{fs}	V _{DS} = 10V, I _D = 12A	8	16		S
Diode forward voltage	V _{DSF}	I _{DR} = 25A, V _{GS} = 0			-1.7	V
Input capacitance (Common Source)	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		1200		pF
Output capacitance (Common Source)	C _{oss}				280	pF
Reverse transfer capacitance (Common Source)	C _{rss}				110	pF
Turn-on time (delay time)	t _{d(on)}	V _{DD} = 30V, I _D = 12A V _{GS} = 10V, R _L = 2.5Ω		8		ns
Rise time	t _r				7	ns
Fall time	t _f				110	ns
Turn-off time (delay time)	t _{d(off)}				330	ns
Thermal resistance between channel and case	R _{th(ch-c)}				12.5	°C/W
Thermal resistance between channel and atmosphere	R _{th(ch-a)}				125	°C/W

